



PSMN6R4-30MLD

N-channel 30 V, 6.4 mΩ logic level MOSFET in LFAK33 using NextPowerS3 Technology

5 July 2017

Product data sheet

1. General description

Logic level gate drive N-channel enhancement mode MOSFET in LFAK33 package. NextPowerS3 portfolio utilising NXP's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- Ultra low Q_G , Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 μA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads for optimal visual solder inspection

3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- Brushed and brushless motor control

4. Quick reference data

Table 1. Quick reference data

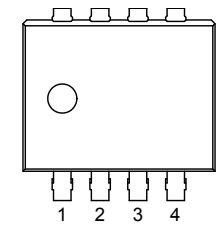
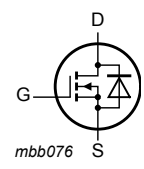
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$	-	-	30	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; Fig. 2	-	-	66	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; Fig. 1	-	-	51	W
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 15\text{ A}$; $T_j = 25\text{ °C}$; Fig. 10	-	6.9	8.3	mΩ

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q _{GD}	gate-drain charge	I _D = 15 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13	-	1.8	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>LPAK33 (SOT1210)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R4-30MLD	LPAK33	Plastic single ended surface mounted package (LPAK33); 8 leads	SOT1210

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN6R4-30MLD	6D430L

8. Limiting values

Table 5. Limiting values

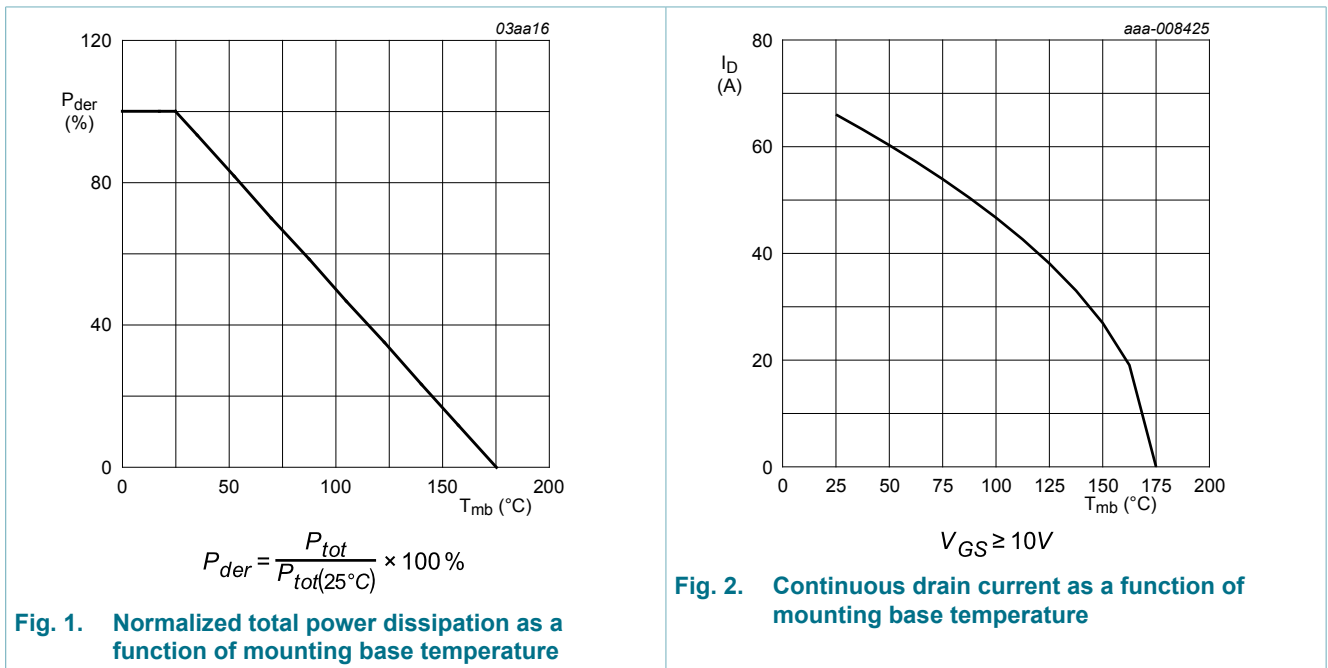
In accordance with the Absolute Maximum Rating System (IEC 60134).

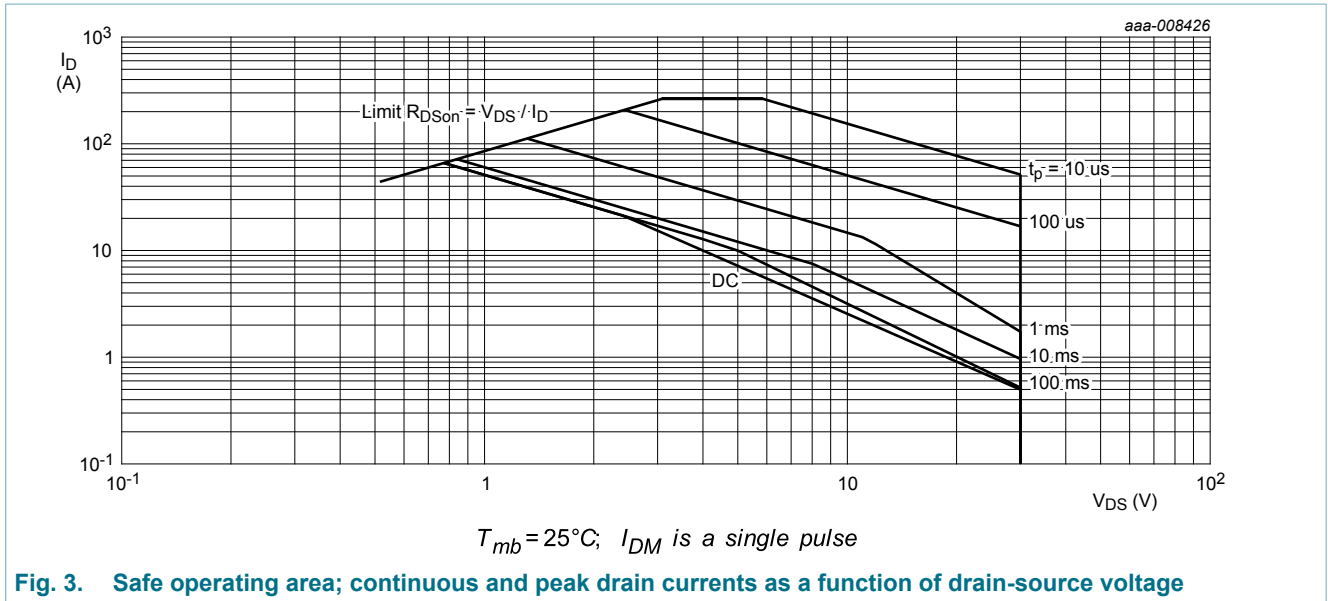
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	30	V
V _{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; Fig. 1	-	51	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; Fig. 2	-	66	A
		V _{GS} = 10 V; T _{mb} = 100 °C; Fig. 2	-	47	A

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Symbol	Parameter	Conditions	Min	Max	Unit
I_{DM}	peak drain current	pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25 \text{ }^\circ\text{C}$; Fig. 3	-	264	A
T_{stg}	storage temperature		-55	175	$^\circ\text{C}$
T_j	junction temperature		-55	175	$^\circ\text{C}$
$T_{sld(M)}$	peak soldering temperature		-	260	$^\circ\text{C}$
Source-drain diode					
I_S	source current	$T_{mb} = 25 \text{ }^\circ\text{C}$	-	43	A
I_{SM}	peak source current	pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25 \text{ }^\circ\text{C}$	-	264	A
Avalanche ruggedness					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$I_D = 15 \text{ A}$; $V_{SUP} \leq 30 \text{ V}$; $R_{GS} = 50 \Omega$; $V_{GS} = 10 \text{ V}$; $T_{j(init)} = 25 \text{ }^\circ\text{C}$; unclamped; $t_p = 159 \mu s$	[1]	-	46.6 mJ

[1] Protected by 100% test

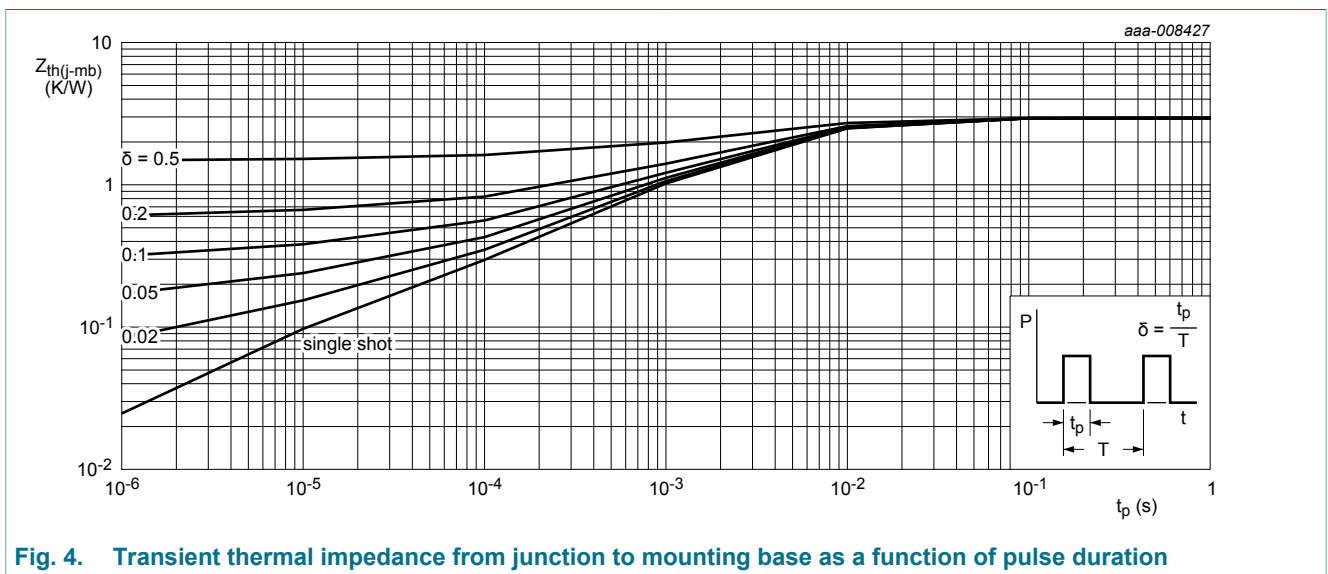


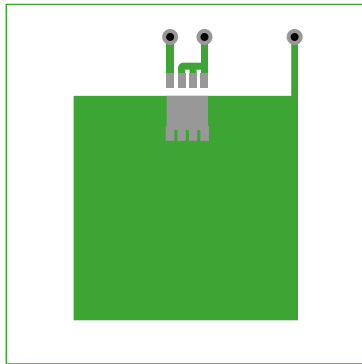


9. Thermal characteristics

Table 6. Thermal characteristics

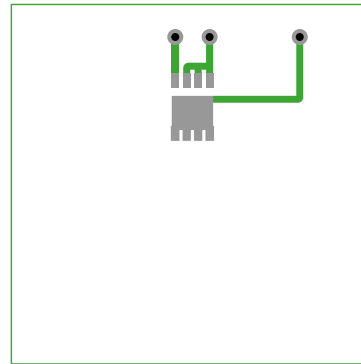
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 4	-	2.72	2.94	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5	-	57	-	K/W
		Fig. 6	-	178	-	K/W





aaa-008476

Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper



aaa-008477

Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint; FR4 Board; 2oz copper

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	30	-	-	V
		$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 \text{ }^\circ C$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ C$	1.2	1.7	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	$25 \text{ }^\circ C \leq T_j \leq 150 \text{ }^\circ C$	-	-3.8	-	mV/K
I_{DSS}	drain leakage current	$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	1	μA
		$V_{DS} = 24 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ C$	-	0.45	-	μA
I_{GSS}	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$	-	-	100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 10	-	6.9	8.3	mΩ
		$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ }^\circ C;$ Fig. 10; Fig. 11	-	-	13.7	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ C;$ Fig. 10	-	5.3	6.3	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 150 \text{ }^\circ C;$ Fig. 10; Fig. 11	-	-	10.4	mΩ
R_G	gate resistance	$f = 1 \text{ MHz}$	-	2.36	-	Ω

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Dynamic characteristics							
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12 ; Fig. 13	-	13.7	-	nC	
		I _D = 15 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13	-	6.5	-	nC	
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	12.2	-	nC	
Q _{GS}	gate-source charge	I _D = 15 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12 ; Fig. 13	-	1.7	-	nC	
Q _{GS(th)}	pre-threshold gate-source charge		-	1.2	-	nC	
Q _{GS(th-pl)}	post-threshold gate-source charge		-	0.5	-	nC	
Q _{GD}	gate-drain charge		-	1.8	-	nC	
V _{GS(pl)}	gate-source plateau voltage	I _D = 15 A; V _{DS} = 15 V; Fig. 12 ; Fig. 13	-	2.2	-	V	
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz; T _j = 25 °C; Fig. 14	-	832	-	pF	
C _{oss}	output capacitance		-	587	-	pF	
C _{rss}	reverse transfer capacitance		-	64	-	pF	
t _{d(on)}	turn-on delay time		V _{DS} = 15 V; R _L = 1 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 5 Ω	-	9	-	ns
t _r	rise time		-	16.2	-	ns	
t _{d(off)}	turn-off delay time		-	10.5	-	ns	
t _f	fall time		-	10.9	-	ns	
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 15 V; f = 1 MHz; T _j = 25 °C	-	12.6	-	nC	
Source-drain diode							
V _{SD}	source-drain voltage	I _S = 10 A; V _{GS} = 0 V; T _j = 25 °C; Fig. 15	-	0.8	1.2	V	
t _{rr}	reverse recovery time	I _S = 15 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 15 V; Fig. 16	-	23.4	-	ns	
Q _r	recovered charge		[1]	-	12.6	-	nC
t _a	reverse recovery rise time		-	-	10.6	-	ns
t _b	reverse recovery fall time		-	-	12.8	-	ns
S	softness factor		-	-	1.2	-	

[1] includes capacitive recovery

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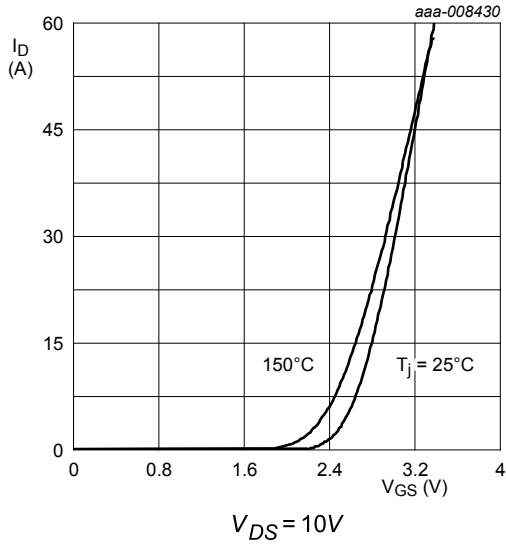


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

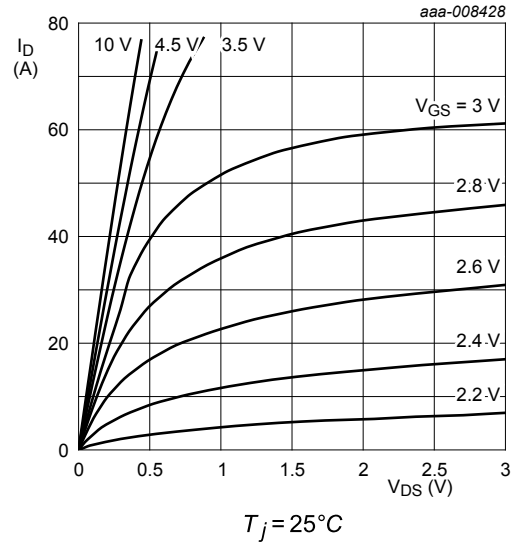


Fig. 8. Output characteristics; drain current as a function of drain-source voltage; typical values

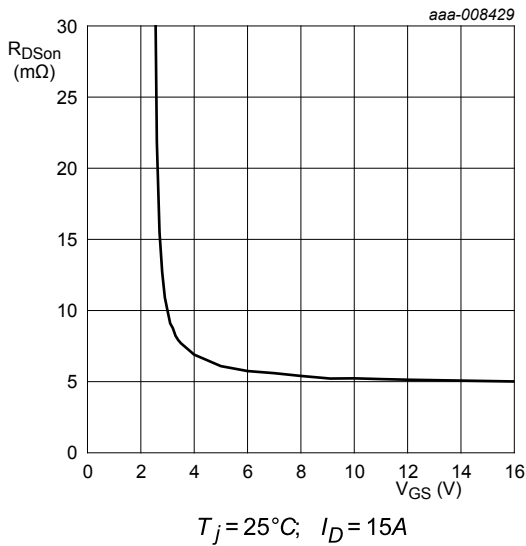


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

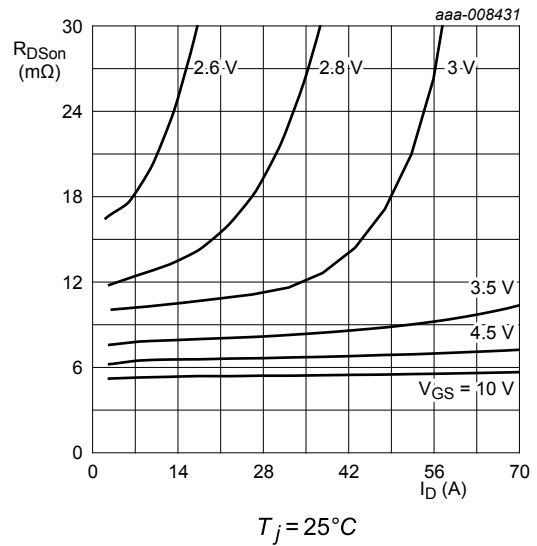
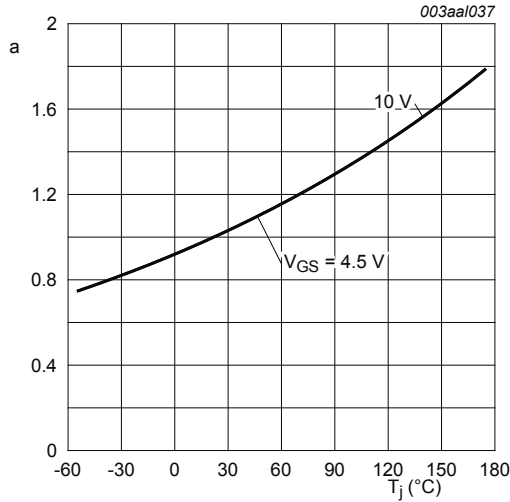


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon}(25^{\circ}\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

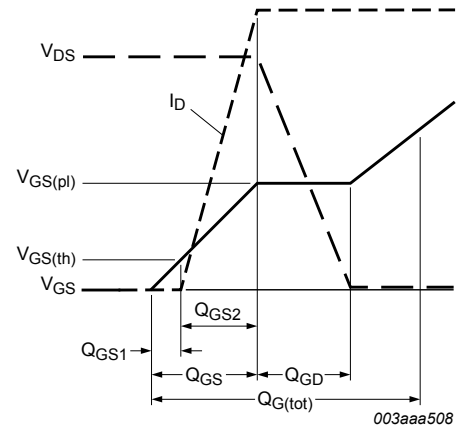


Fig. 12. Gate charge waveform definitions

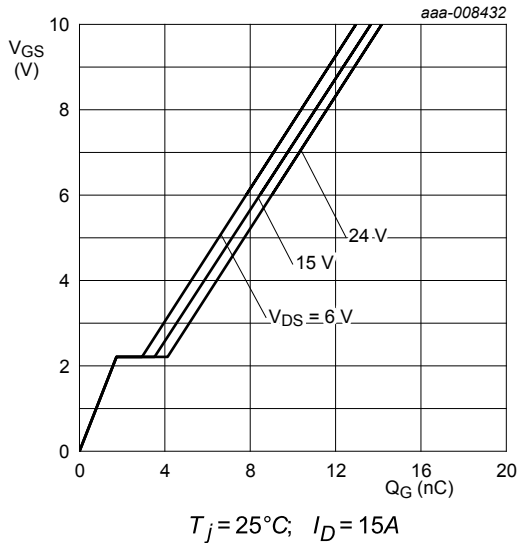


Fig. 13. Gate-source voltage as a function of gate charge; typical values

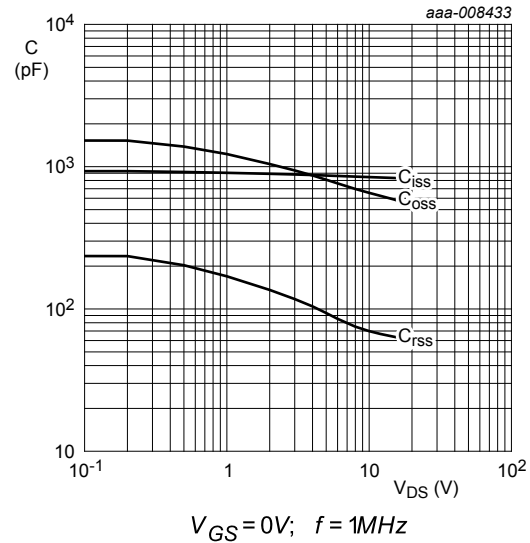


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

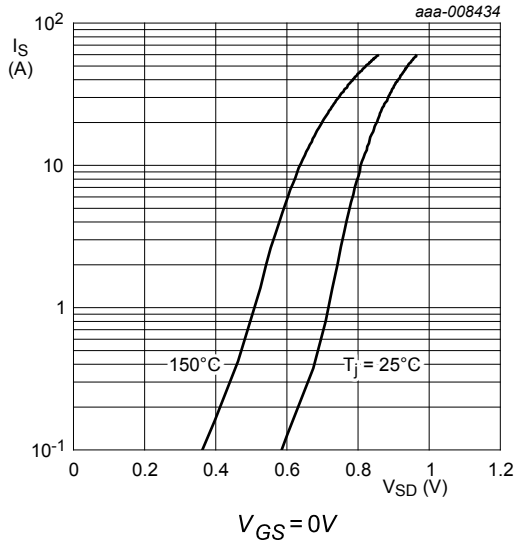


Fig. 15. Source current as a function of source-drain voltage; typical values

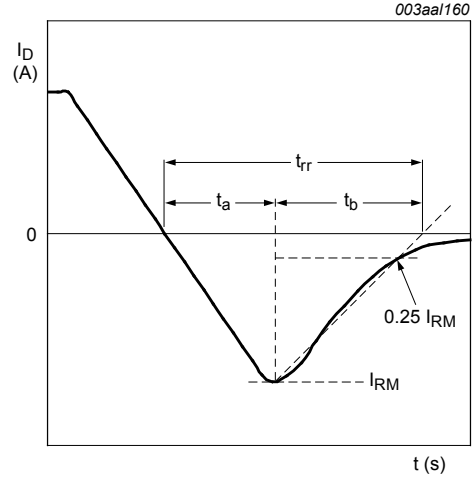


Fig. 16. Reverse recovery timing definition

11. Package outline

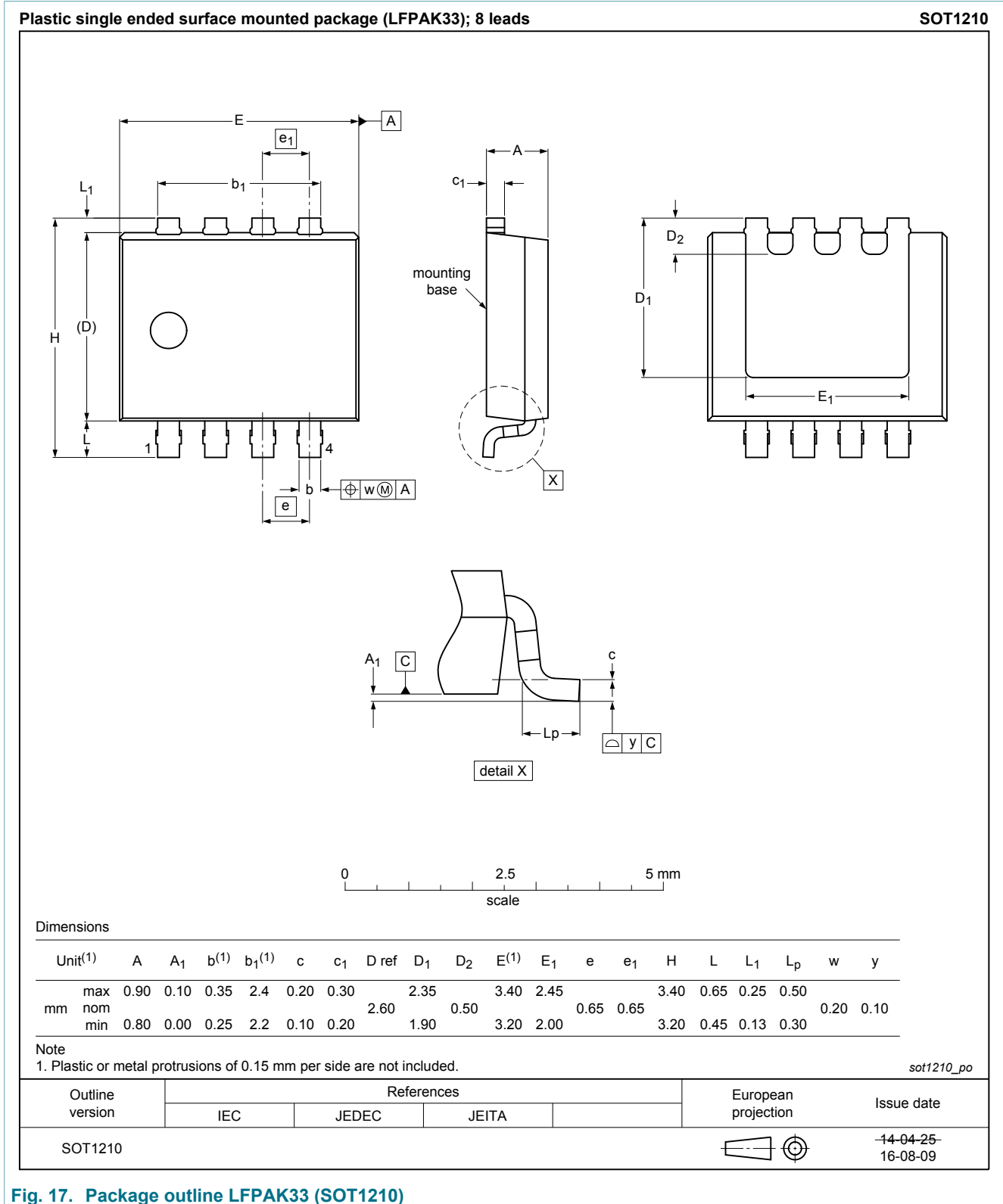


Fig. 17. Package outline LPAK33 (SOT1210)

12. Soldering

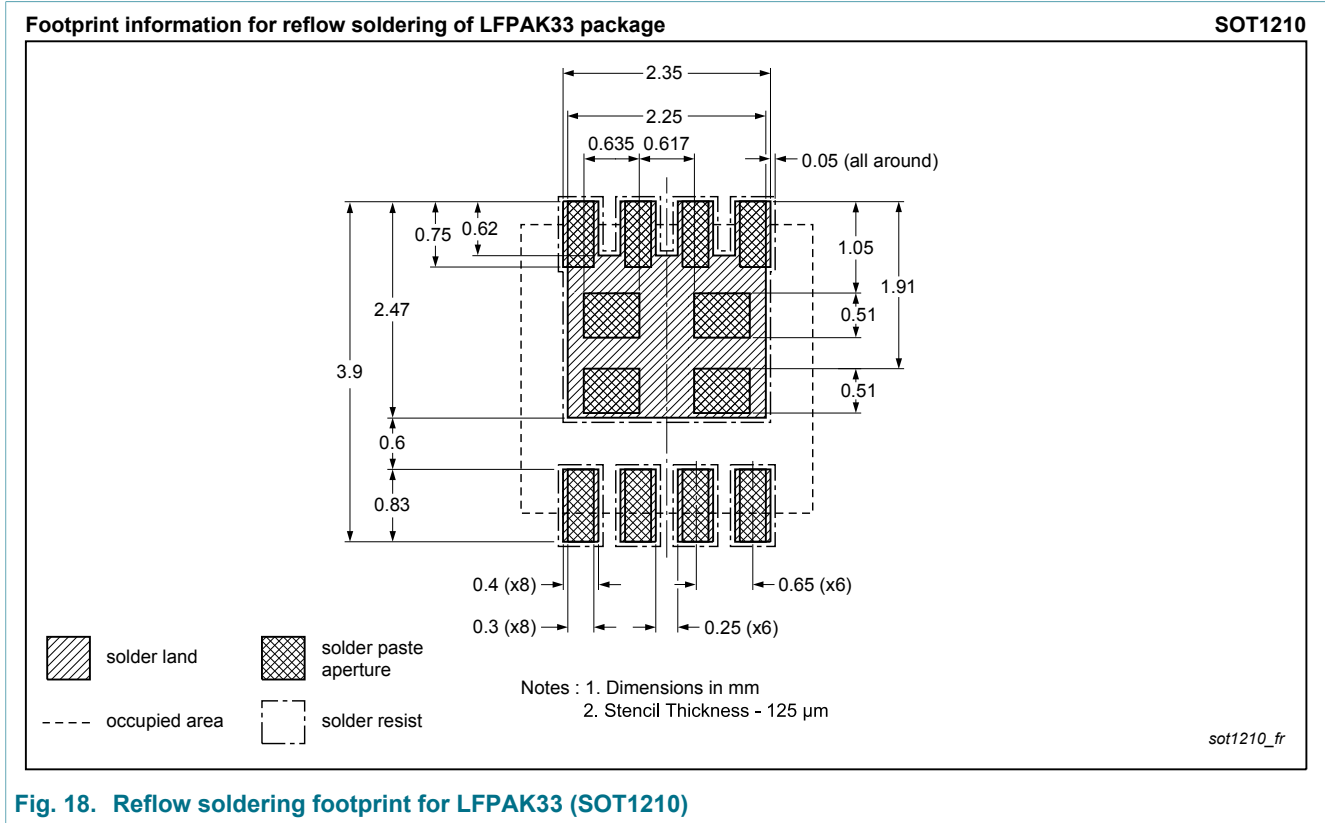


Fig. 18. Reflow soldering footprint for LPAK33 (SOT1210)

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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